

KBP200G – KBP2010G

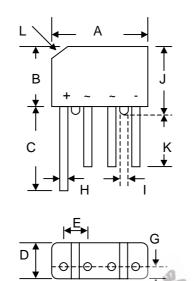
2.0A GLASS PASSIVATED BRIDGE RECTIFIER

Features

- Glass Passivated Die Construction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability
- Ideal for Printed Circuit Boards

Mechanical Data

- Case: Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: As Marked on Body
- Weight: 1.7 grams (approx.)
- Mounting Position: Any
- Marking: Type Number



KBP				
Dim	Min	Max		
Α	14.22	15.24		
В	10.67	11.68		
С	15.2	—		
D	4.57	5.08		
E	3.60	4.10		
G	2.16	2.67		
Н	0.76	0.86		
I	1.52 —			
J	11.68 12.7			
к	12.7 —			
L	3.2 x 45° Typical			
All Dimensions in mm				

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

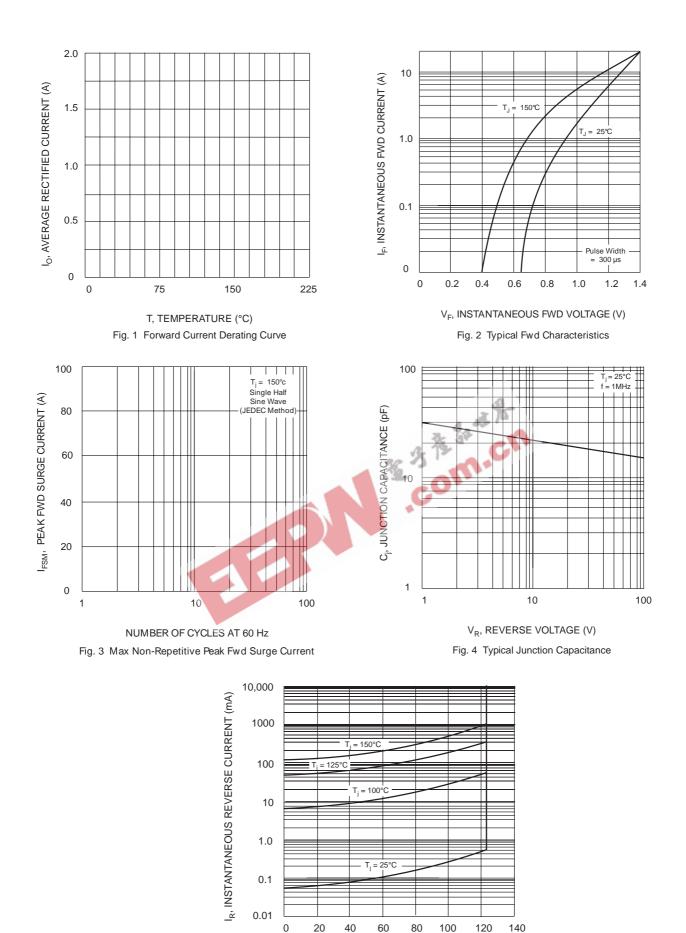
Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	KBP 200G	KBP 201G	KBP 202G	KBP 204G	KBP 206G	KBP 208G	KBP 2010G	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	Vrrm Vrwm Vr	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	VR(RMS)	35	70	140	280	420	560	700	V
Average Rectified Output Current (Note 1) $@T_A = 50^{\circ}C$	lo				2.0				A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM				60				A
Forward Voltage (per element) $@I_F = 2.0A$	Vfm				1.1				V
Peak Reverse Current $@T_A = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_A = 100^{\circ}C$					10 500				μA
Rating for Fusing (t<8.3ms)	l ² t				15				A ² s
Typical Junction Capacitance per element (Note 2)	Cj	25				pF			
Typical Thermal Resistance (Note 3)	RθJA	30					K/W		
Operating and Storage Temperature Range	Tj, TSTG	-55 to +165				°C			

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case.

2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

3. Thermal resistance junction to ambient mounted on PC board with 12mm² copper pad.



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PERCENT OF RATED PEAK REVERSE VOLTAGE (%) Fig. 5 Typical Reverse Characteristics

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ORDERING INFORMATIO	ON
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Product No.	Package Type	Shipping Quantity
KBP200G	SIL Bridge	1000 Units/Box
KBP201G	SIL Bridge	1000 Units/Box
KBP202G	SIL Bridge	1000 Units/Box
KBP204G	SIL Bridge	1000 Units/Box
KBP206G	SIL Bridge	1000 Units/Box
KBP208G	SIL Bridge	1000 Units/Box
KBP2010G	SIL Bridge	1000 Units/Box

Shipping quantity given is for minimum packing quantity only. For minimum order quantity, please consult the Sales Department.



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